Silicon Carbide (SiC) Schottky Diode - EliteSiC, 6 A, 650 V, D1, D2PAK-2L

FFSB0665A

Description

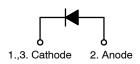
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

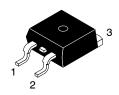
- Max Junction Temperature 175°C
- Avalanche Rated 36 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

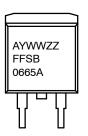


Schottky Diode



D2PAK-2L (TO-263-2L) CASE 418BK

MARKING DIAGRAM



A = Assembly Location YWW = Data Code (Year & Week)

ZZ = Lot Code

FFSB0665A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	650	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	36	mJ	
lF	Continuous Rectified Forward Current @ T _C < 152°C		6	Α
	Continuous Rectified Forward Current @ T _C <	9		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	430	Α
		T _C = 150°C, 10 μs	415	Α
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	42	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	24	Α
Ptot	Power Dissipation	T _C = 25°C	65	W
		T _C = 150°C	11	W
T _J , T _{STG}	Operating and Storage Temperature Range	•	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	2.3	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 6 A, T _C = 25°C	-	1.50	1.75	V
		I _F = 6 A, T _C = 125°C	-	1.6	2.0	
		I _F = 6 A, T _C = 175°C	-	1.72	2.4	
I _R	Reverse Current	$V_R = 650 \text{ V}, T_C = 25^{\circ}\text{C}$	-	-	200	μΑ
		V _R = 650 V, T _C = 125°C	-	-	400	
		V _R = 650 V, T _C = 175°C	-	-	600	
Q_C	Total Capacitive Charge	V = 400 V	-	22	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	361	-	pF
		V _R = 200 V, f = 100 kHz	-	41	-	
		V _R = 400 V, f = 100 kHz	_	32	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Shipping [†]
FFSB0665A	FFSB0665A	D2PAK-2L (TO-263-2L) Pb-Free/Halogen Free	330 mm	24 mm	800 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} E_{AS} of 36 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 12$ A, V = 50 V.

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TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

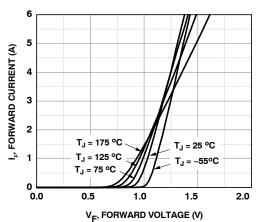


Figure 1. Forward Characteristics

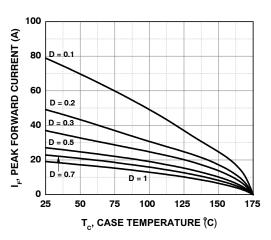


Figure 3. Current Derating

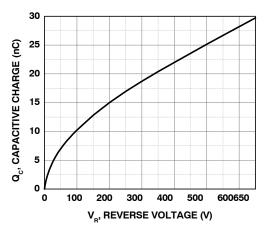


Figure 5. Capacitive Charge vs. Reverse Voltage

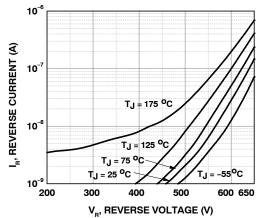


Figure 2. Reverse Characteristics

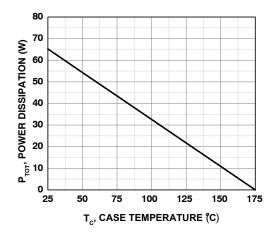


Figure 4. Power Derating

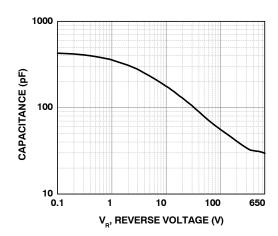


Figure 6. Capacitance vs. Reverse Voltage

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TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

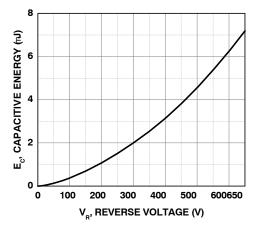


Figure 7. Capacitance Stored Energy

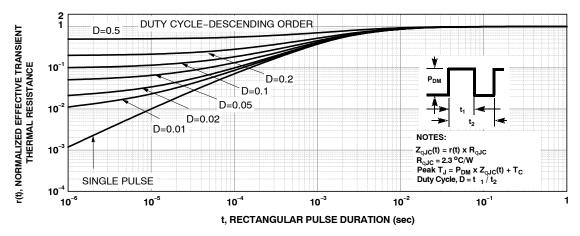
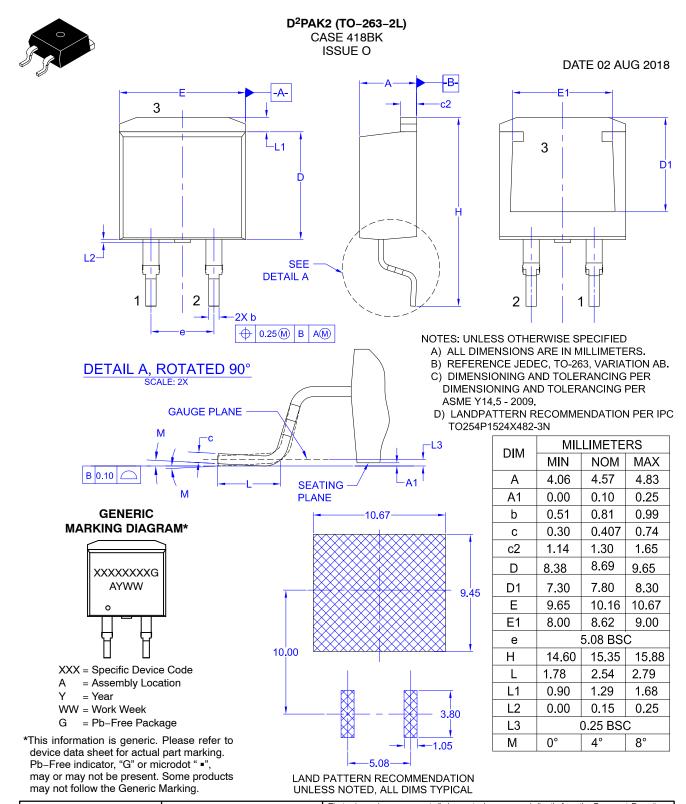


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

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L = 0.5 \text{ mH}
R < 0.1 \Omega
V_{DD} = 50 \text{ V}
EAVL = 1/2LI2 \left[ V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right]
Q1 = IGBT \left( BV_{CES} > DUT \ V_{R(AVL)} \right)
V_{AVL}
V_{DD}
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Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



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